

<b>SANYO</b>	No.3241	<b>2SC4449</b>
		NPN Triple Diffused Planar Silicon Transistor TV Camera Deflection, High-Voltage Driver Applications

**Features**

- High breakdown voltage
- Small reverse transfer capacitance and excellent high frequency characteristic
- Excellent DC current gain
- Adoption of FBET process

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	300	V
Collector to Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter to Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	50	mA
Collector Current(Pulse)	I <sub>CP</sub>	100	mA
Collector Dissipation	P <sub>C</sub>	600	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

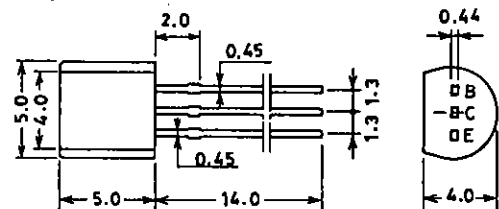
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 200V, I <sub>E</sub> = 0			0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0			0.1	μA
DC Current Gain	h <sub>FE</sub> (1)	V <sub>CE</sub> = 6V, I <sub>C</sub> = 0.1mA	100		320	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = 6V, I <sub>C</sub> = 1mA	100			
DC Current Gain Ratio	h <sub>FE</sub> ratio	h <sub>FE</sub> (1)/h <sub>FE</sub> (2)		0.95		
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 30V, I <sub>C</sub> = 10mA		70		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA			1.0	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA			1.0	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	300			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	300			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	5			V
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> = 30V, f = 1MHz		1.5		pF
Reverse Transfer Capacitance	c <sub>re</sub>	V <sub>CB</sub> = 30V, f = 1MHz		1.0		pF

※ : The 2SC4449 is classified by 0.1mA h<sub>FE</sub> as follows :

100	E	200	160	F	320
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**Package Dimensions 2003A**  
(unit: mm)



JEDEC: TO-92

EIAJ: SC-43

SANYO: NP

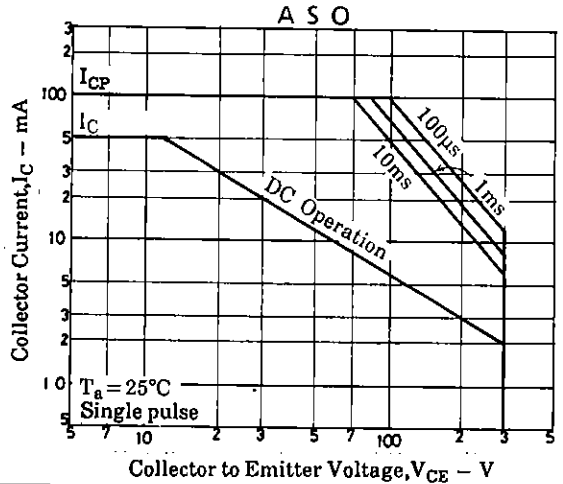
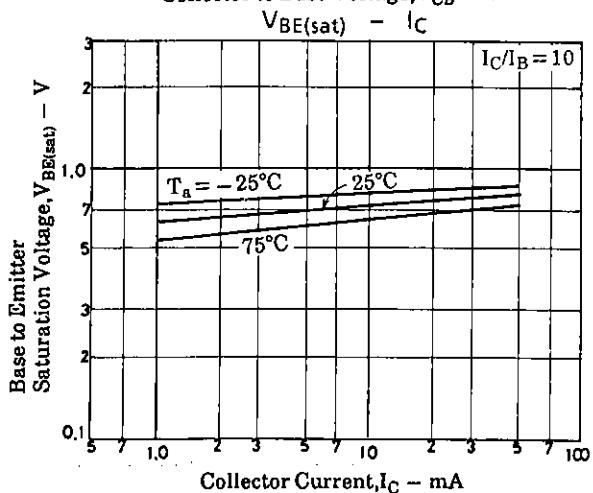
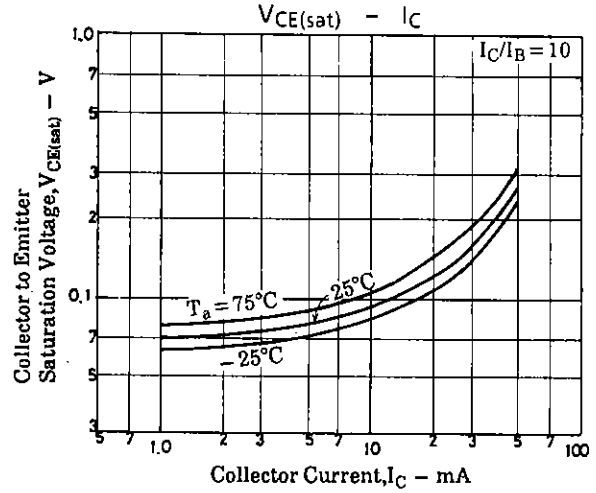
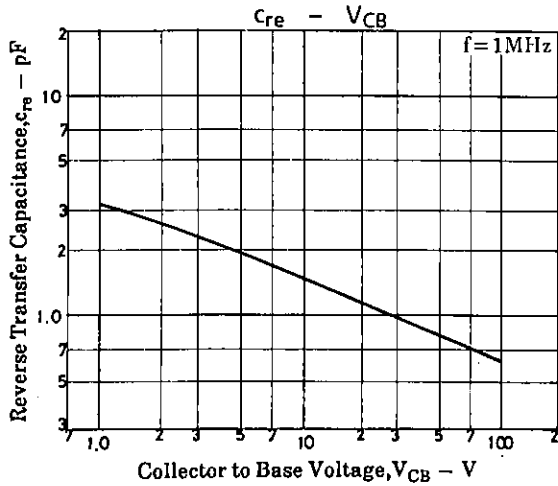
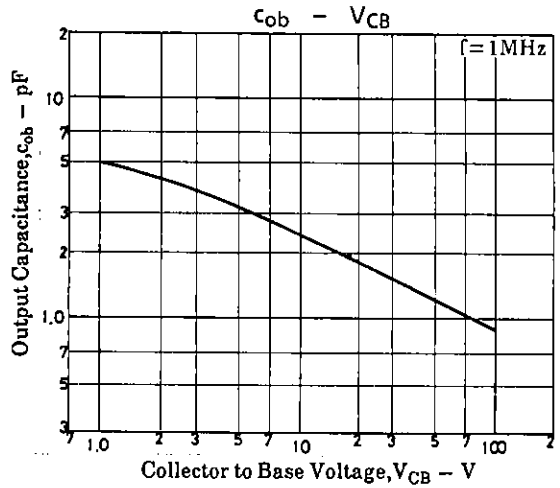
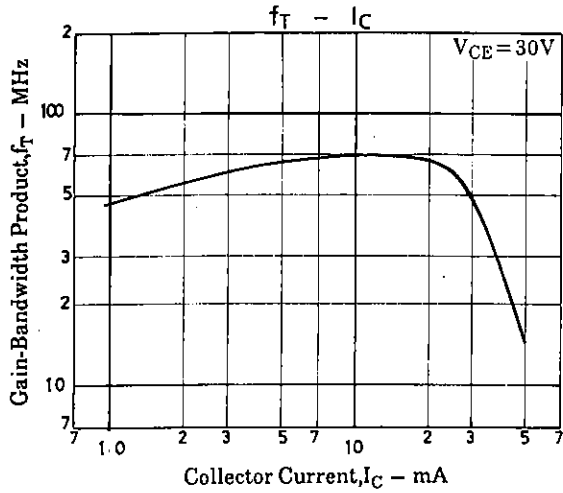
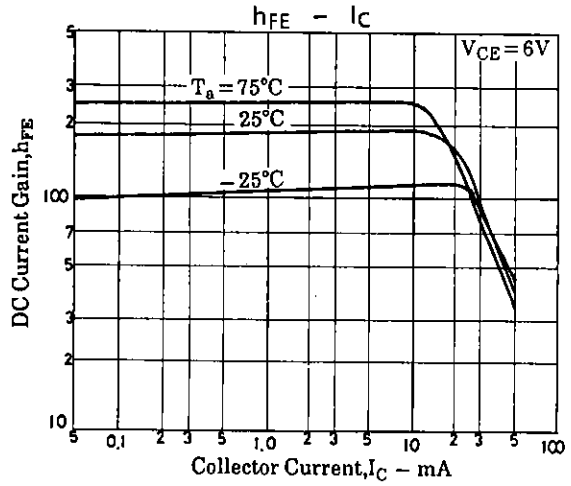
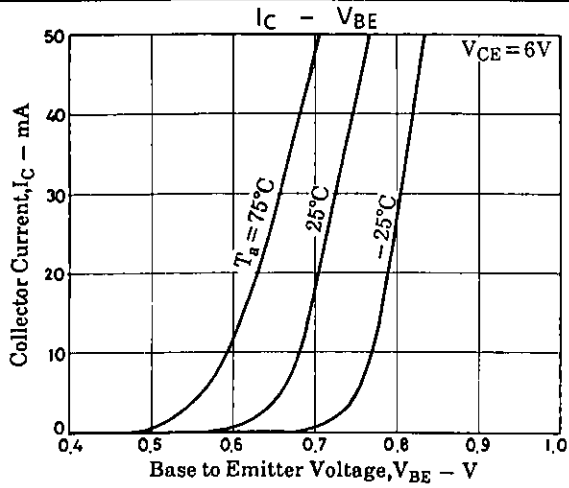
B: Base

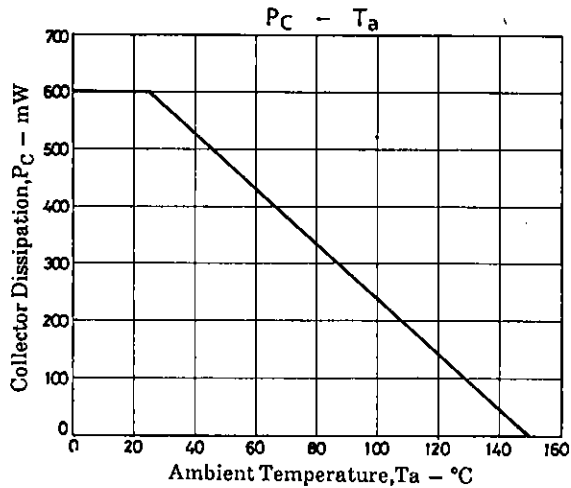
C: Collector

E: Emitter

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